

Extended InGaAs Photodiodes IG19-Series

Description

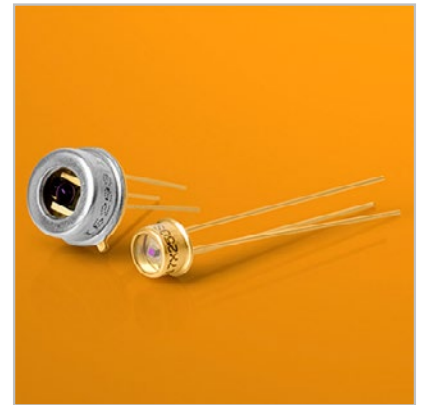
The IG19-series is a panchromatic PIN photodiode with a nominal wavelength cut-off at 1.9 μm . This series has been designed for demanding spectroscopic and radiometric applications. It offers excellent shunt resistance in combination with superior responsivity over a wide range.

Features

- 50 % cut-off wavelength $\geq 1.87 \mu\text{m}$
- Typical peak responsivity: 1.15 A/W
- Excellent temperature stability
- Reduced edge effect

Applications

- Spectrophotometer
- Diode laser monitoring



Optical Characteristics, Specifications @ 25°C ^c

Part Number	Diameter [μm]	50% Cut off Wavelength ^a [μm]	Peak Wa- velength ^a [μm]	Peak Responsivity ^a [A/W]		Responsivity @ 520 nm ^{a,d} [A/W]		Responsivity @ 1500 nm ^a [A/W]		Responsivity @ 1700 nm ^a [A/W]	
				Min.	Typ.	Min.	Typ.	Min.	Typ.	Min.	Typ.
IG19X250S4i	250	1.87	1.75	1.1	1.15	TBD	0.1	0.77	0.96	0.9	1.05
IG19X1000S4i	1000	1.87	1.75	1.1	1.15	TBD	0.1	0.77	0.96	0.9	1.05

^a Parameter tested on batch level.

^b Responsivity measured at 0 V Bias.

^c Data are prior to window integration.

^d Preliminary data.

Electro-Optical Characteristics, Specifications @ 25°C

Part Number	Diameter [μm]	Shunt Impedance @ V _R = 10 mV ^b [MOhm]		Dark Current @ V _R = 0.25 V ^b [nA]		Peak D* ^a [cm Hz ^{1/2} /W]		Peak NEP ^a [W/Hz ^{1/2}]		Capacitance @ V _R = 0 V ^a [pF]
		Min.	Typ.	Typ.	Max.	Min.	Typ.	Typ.	Max.	Typ.
IG19X250S4i	250	8.0	16	5	50	1.2 E12	1.7 E+12	2.9 E-14	4.1 E-14	60
IG19X1000S4i	1000	0.8	1.6	40	400	7.6 E+11	1.1 E+12	0.9 E-13	1.3 E-13	1040

^a Parameter tested on batch level

^b Parameter 100% tested

Thermoelectrically Cooled InGaAs Detectors

Part Number	Diameter [μm]	Operating Temperature [°C]	Shunt Impedance @ V _R = 10 mV ^b [MOhm]		Peak D* ^a [cm Hz ^{1/2} /W]	Peak NEP ^a [W/Hz ^{1/2}]	Capacitance @ V _R = 0 V ^a [pF]
			Min.	Typ.			
IG19X1000T7	1000	-20	30	105	8.8E+12	1.1E-14	1040
IG19X1000T9	1000	-40	160	400	1.5E+13	6.6E-15	1040

^a Parameter tested on batch level

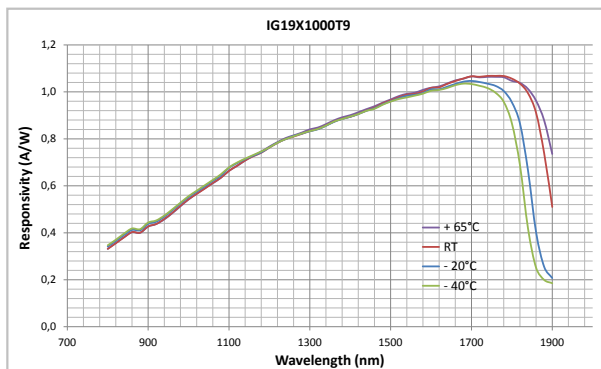
^b Parameter 100% tested

Absolute Maximum Ratings

		Min.	Max.
Storage Temperature [°C]		-55	+125°
Operating Temperature [°C]		-40	+85
Reverse Bias, cw [V]		-	1
Forward Current, cw [mA]		-	1
Soldering Temperature, 5 sec. [°C]		-	260
ESD Damage Threshold, Human Body Model Class 0*, [V]		0	<250
TE Cooler Voltage [V]	T7	-	0.8
	T9	-	3.7
TE Cooler Current [A]	T7	-	1.9
	T9	-	1.2

*ANSI/ ESD STN5. 1-2007

Fig. 1: Spectral Response



Nomenclature

C-	I	G	1	9	X	1	0	0	0	S	4	i	
Chip only	Type					Diameter				Package Style			
	Extended InGaAs PIN Photodiode					250 = 250 µm				S4i - TO-46, isolated			
						1000 = 1 mm				S4ix - TO-46, no window			
										G1i - TO-39, isolated			
										G1ix - TO-39, no window			
										T7 - TO-37, single stage TEC			
										T9 - TO-66, dual stage TEC			
										M2 - 2 pad PCB SMD			
										L5 - TO-46 lens cap			

Standard window: Borosilicate glass

Package drawings, TEC and thermistor curves can be found on a separate datasheet.

Product Changes

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Ordering Information

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